

[Document]            ABSTRACT

[Abstract]

[Object]   An object of the present invention is to improve a characteristic and reliability of a semiconductor device having a Cu film for wiring and an Al film for a pad connected to the Cu film.

[Means for Achieving the Object]   There is provided a semiconductor device comprising a Cu film 23 which constitutes a wiring layer, an intermediate layer formed on the Cu film 23, and an Al film 34 formed on the intermediate layer and used as a pad layer, wherein the intermediate layer comprises a first metal film having a high melting point 33a, a metal nitride film having a high melting point 33b formed on the first metal film having a high melting point 33a, and a second metal film having a high melting point 33c formed on the metal nitride film having a high melting point 33b.

[Elected Figure]   FIG. 3